

Supplementary Information:

m-BiVO₄@ γ -Bi₂O₃ core-shell p-n heterogeneous nanostructure for enhanced visible-light photocatalytic performance

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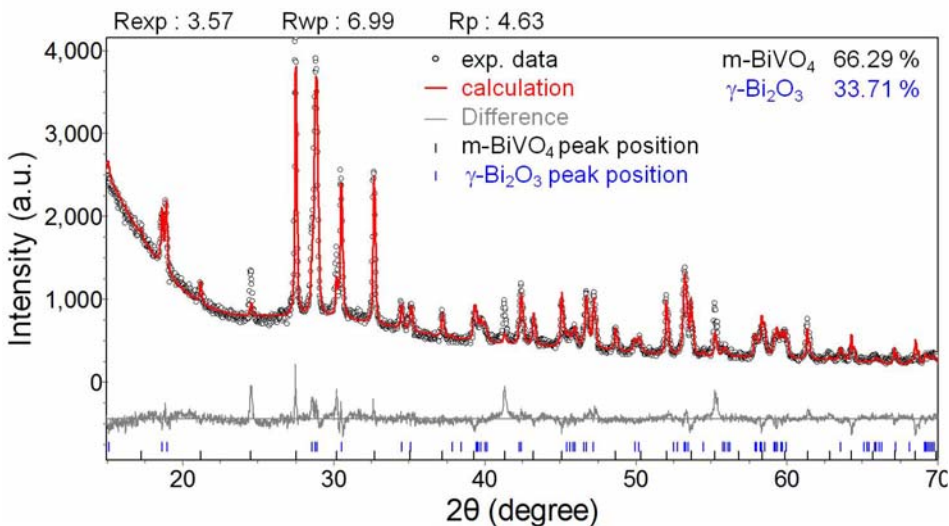
Part 1 XRD refinement

Rietveld refinement details (BB03 as an example):

The Rietveld analysis of BB03 XRD data was conducted by using TOPAS (Version 3, Bruker). Prior to the structural refinement, the X-ray emission profile, instrument parameters and Lorentz-Polarisation factor were corrected according to the instrument conditions, and there parameters were fixed without further refinement. Then, a Chebychev polynomial of 7th order was used to fit the XRD curve background, and the zero point error correction was selected in the latter global curve refinement. For the quantitative analysis, the structure files (.cif) of *m*-BiVO₄ and γ -Bi₂O₃ were imported to the software. The structure details are listed in Table S1. Then the quantitative profile refinement was conducted in which the unit cell parameters (*a*, *b*, *c* and β for *m*-BiVO₄ and *a* for γ -Bi₂O₃), phase scales, crystal size, background, preferred orientation ((004) for *m*-BiVO₄ and (222) for γ -Bi₂O₃) were refined together to give the final agreement factors of *R*_p = 4.63%, *R*_{wp} = 6.99%, and *R*_{exp} = 3.57%. The atomic coordinates for both crystal phases were not further refined. The resultant phase ratio of BB03 was 66.29% of *m*-BiVO₄ and 33.71% of γ -Bi₂O₃ as list in SI Table 1 in the text. The Rietveld refined pattern was shown in SI Figure 1.

SI Table 1 The crystal structure of *m*-BiVO₄ and γ -Bi₂O₃.

	<i>m</i> -BiVO ₄ [1]	γ -Bi ₂ O ₃ [2]
Space Group	I112/b	I23
Crystal System	monoclinic	Cubic
Unit Cell	$a = 5.197 \text{ \AA}$ $b = 11.702 \text{ \AA}$ $c = 5.096 \text{ \AA}$ $\beta = 90.4^\circ$	$a = 10.267 \text{ \AA}$
Cell Volume	$309.91 \text{ \AA}^3$	$1082.57 \text{ \AA}^3$
Z	4	13



SI Figure 1 Rietveld refinement of sample BB03.

Part 2 Diffuse reflectance spectrum (DRS) study and band structure estimation.

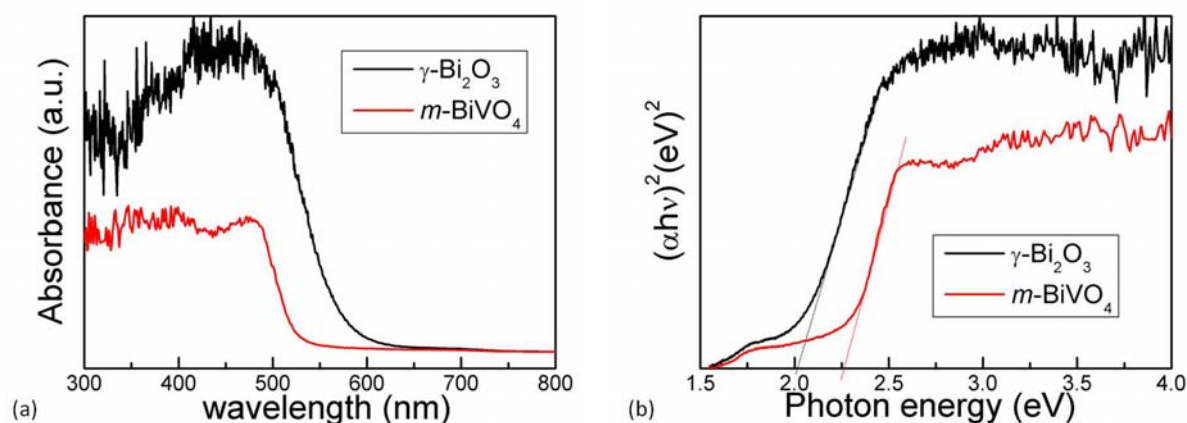
For the two pure oxides, the band edge positions of their conduction band (CB) and valence band (VB) at the point of zero charge (pH_{zpc}) can be predicted by the empirical equation:

$$E_{\text{CB}}^0 = X - E^c - 1/2 E_g$$

where E_{CB}^0 is the CB edge potential; X is the absolute electronegativity of the semiconductor, which is the geometric mean of the absolute electronegativity of the constituent atoms (X values for BiVO₄ and Bi₂O₃ are 6.04 and 5.95 eV, respectively); E^c is the energy of free electrons on the hydrogen scale (about 4.5 eV); and E_g is the band gap of the semiconductor. So the predicted band edge positions of Bi₂O₃ and BiVO₄ by the above equation are shown in below SI Table 2, and schematically illustrated in Figure 6 (a).

SI Table 2 Absolute electronegativity, estimated band gap, calculated energy levels of conduction band edge and valence band edge at the zero-charge point for *m*-BiVO₄ and γ -Bi₂O₃.

Oxide Material	X, Absolute Electronegativity	Estimated Band Gap (eV)	Calculated CB (eV)	Calculated VB (eV)
BiVO ₄	6.04	2.26	0.41	2.67
Bi ₂ O ₃	5.95	2.04	0.43	2.47



SI Figure 2 (a) UV-Vis diffuse reflectance spectrum of the as prepared *m*-BiVO₄ and γ -Bi₂O₃ samples, and (b) plots of $(\alpha h\nu)^2$ versus $h\nu$, by which the values of the energy band gaps of the samples, corresponding to those in (a).

Part 3 Surface photovoltage (SPV) measurement:

The CPD is defined as:

$$e \cdot \text{CPD} = W_s - W_m$$

where W_s is the surface work function of sample powders and W_m is Kelvin probe work function, which was calibrated on Au surface. The ΔCPD is defined as:

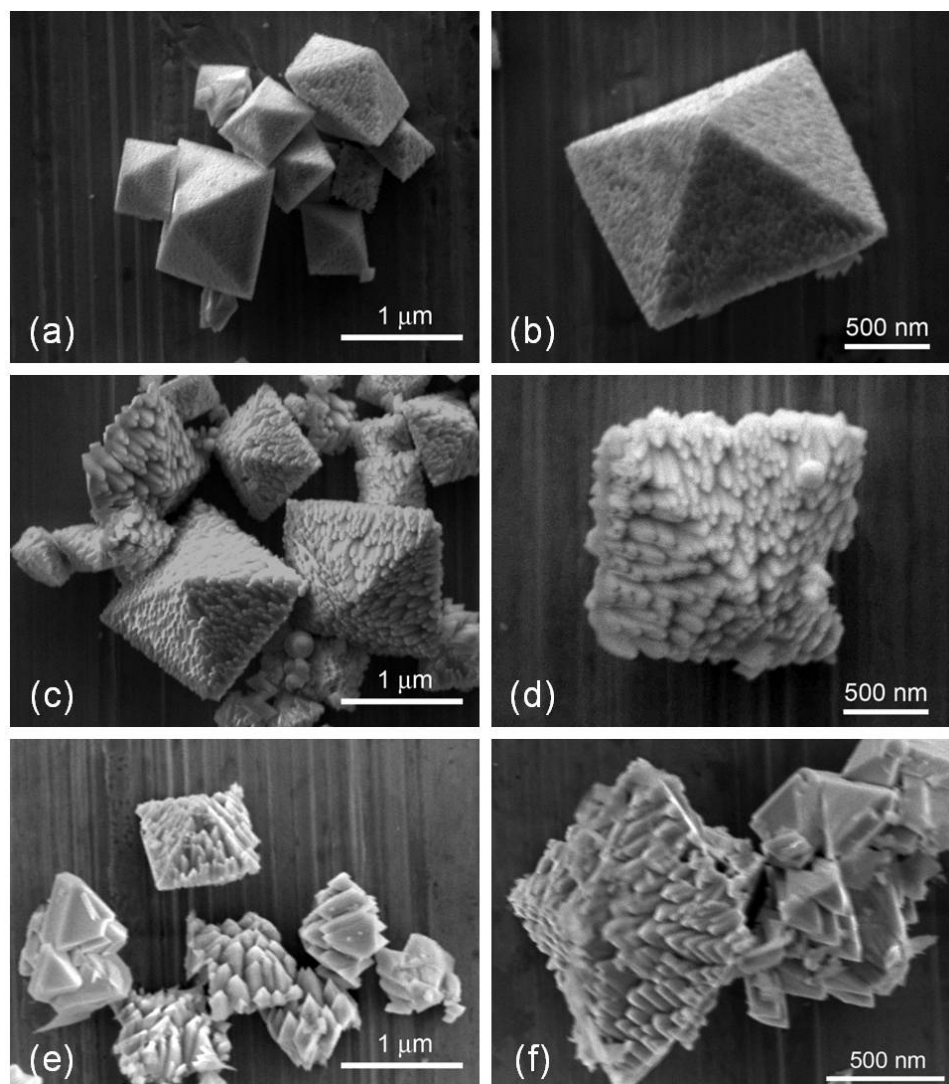
$$\Delta\text{CPD} = \text{CPD}_{\text{in dark}} - \text{CPD}_{\text{under illumination}}$$

Since the work function of the probe does not change under illumination, it is assumed that

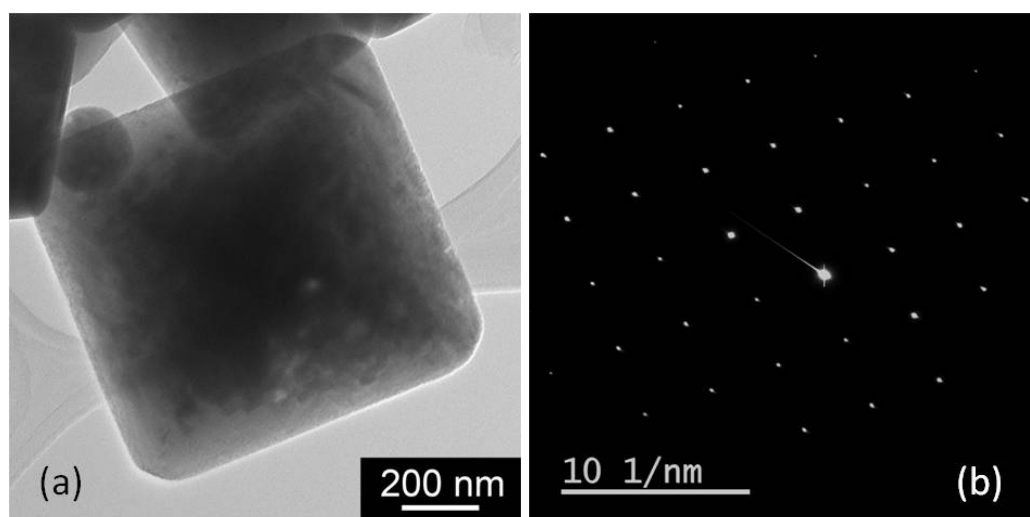
$$e \cdot \Delta\text{CPD} = \Delta W_s = -e \Delta V_s = -e \cdot \text{SPV},$$

where ΔV_s is the change of surface potential, which is the surface photovoltage (SPV) measured in the Kelvin probe system.

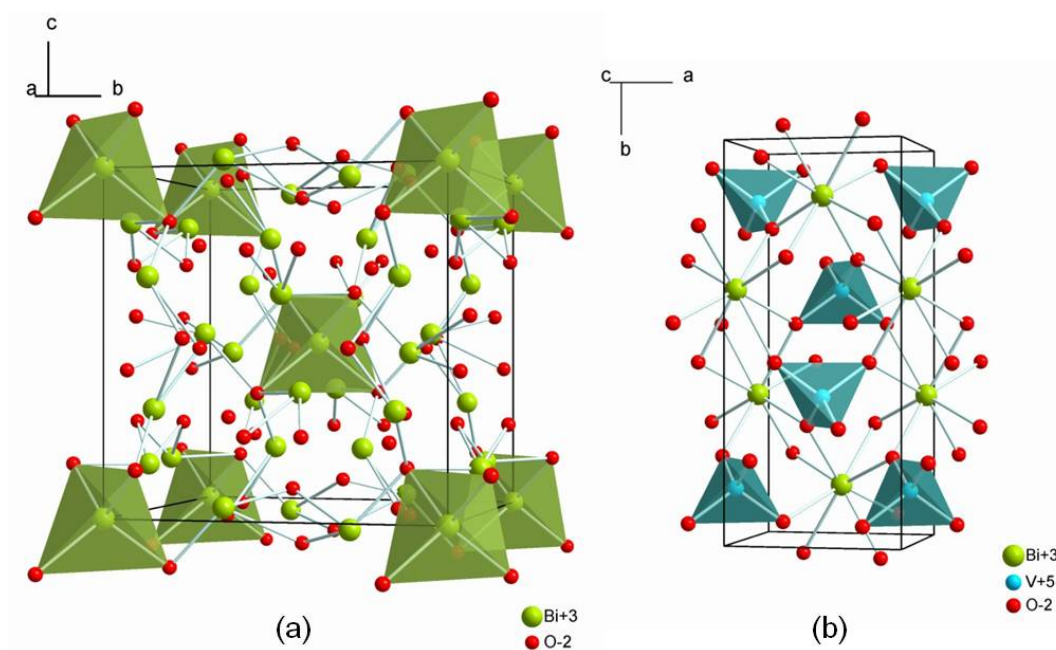
Part 4 Other Figures



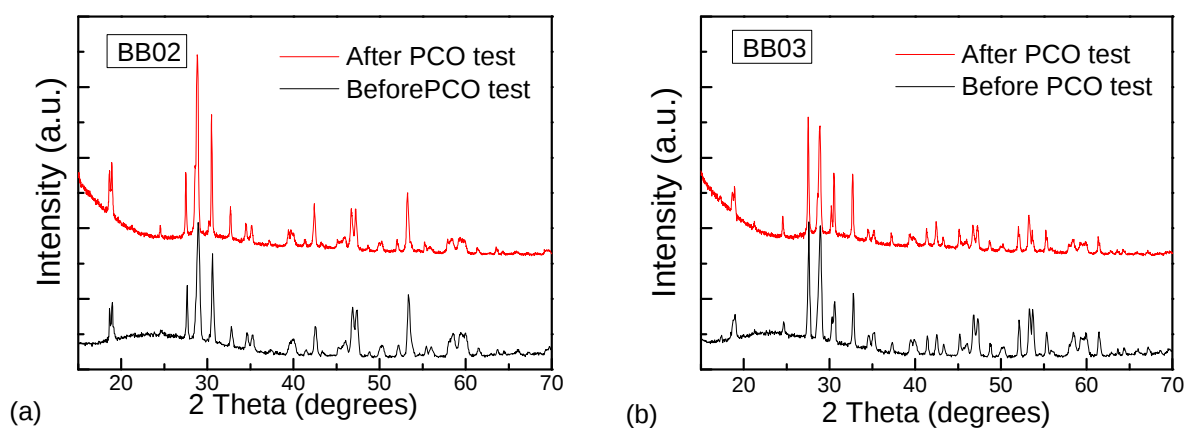
SI Figure 3 SEM images of as-prepared $m\text{-BiVO}_4@ \gamma\text{-Bi}_2\text{O}_3$ particles fabricated under different alkaline concentrations, (a) & (b) 0.1 M BB01, (c) & (d) 0.2 M BB03, (e) & (f) 0.3 M BB04.



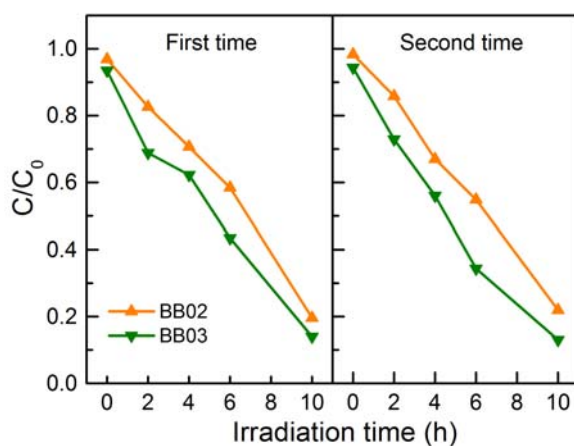
SI Figure 4 (a) TEM image and (b) its corresponding SAED pattern of a pure *m*-BiVO₄ octahedral single crystal.



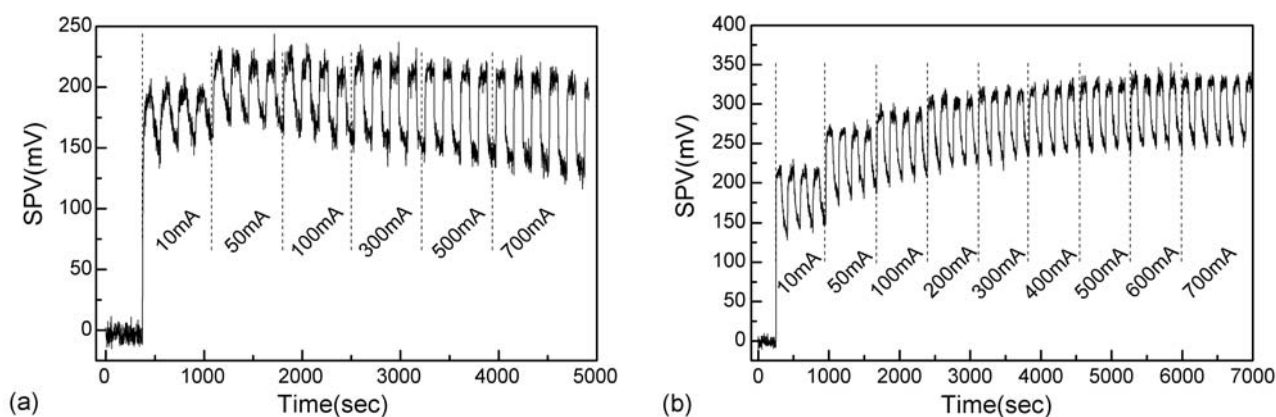
SI Figure 5 Crystal structure comparison between (a) cubic γ -Bi₂O₃ and (b) monoclinic scheelite BiVO₄.



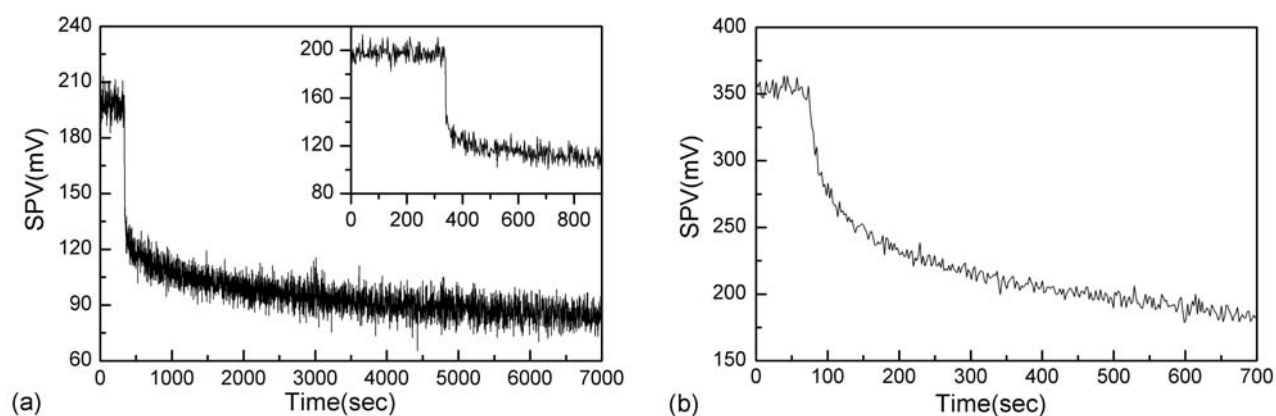
SI Figure 6 XRD patterns of the samples (a) BB02 and (b) BB03 before (lower black) and after (upper red) photocatalytic test in the degradation of RhB.



SI Figure 7 the repeated photocatalytic test of the samples BB02 and BB03 in the degradation of RhB.



SI Figure 8 Transient SPV spectra of (a) pure $m\text{-BiVO}_4$ and (b) BB03.



SI Figure 9 Transient SPV spectra of (a) pure $m\text{-BiVO}_4$ and (b) BB03 after irradiation turned off.

References

- [1] Wu Li, Hsueh Pao, *Acta Physica Sinica*. 32 (1983) 1053-1060.
- [2] Harwig H, *Z. Anorg. Allg. Chem.* 444 (1978) 151-166.